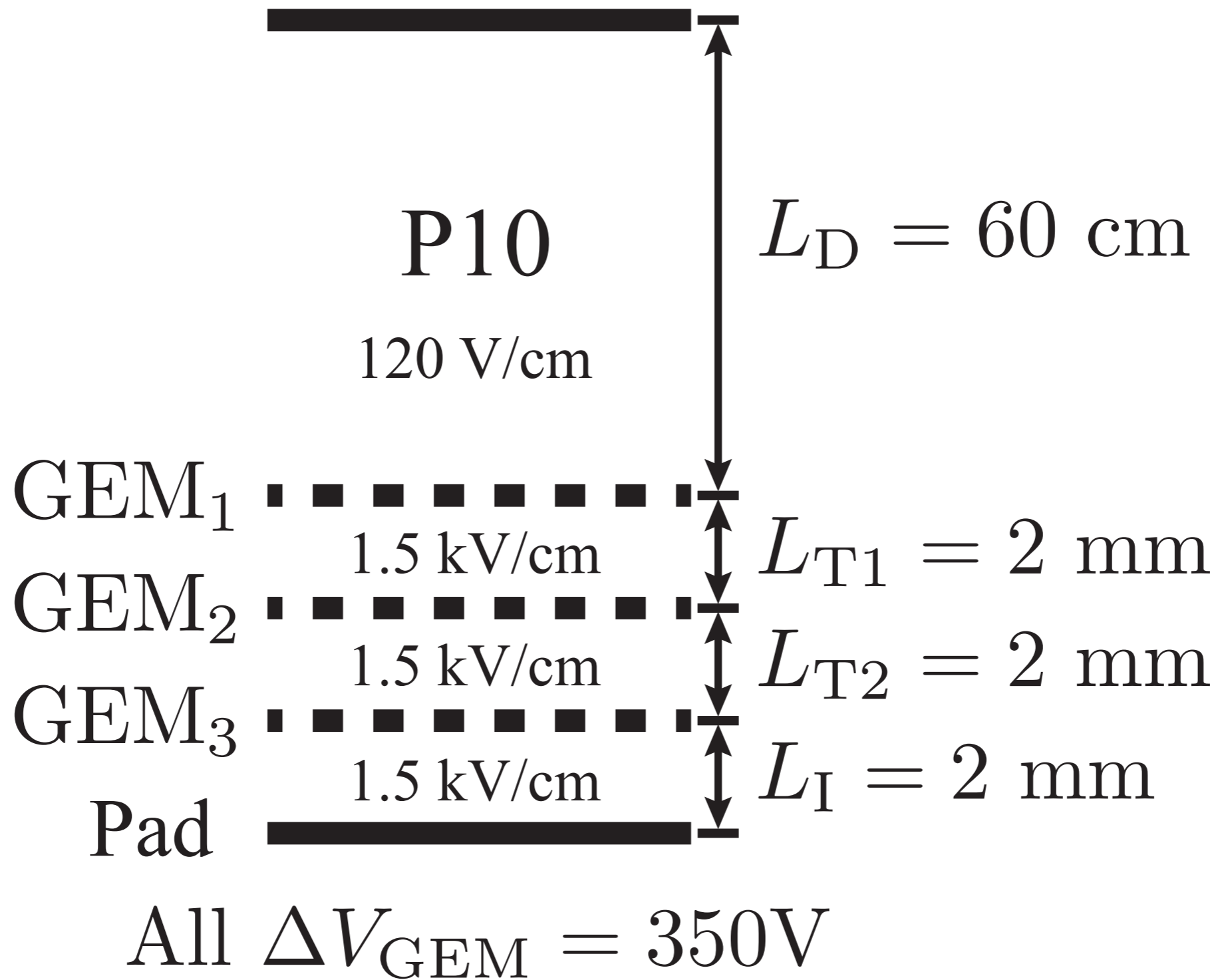
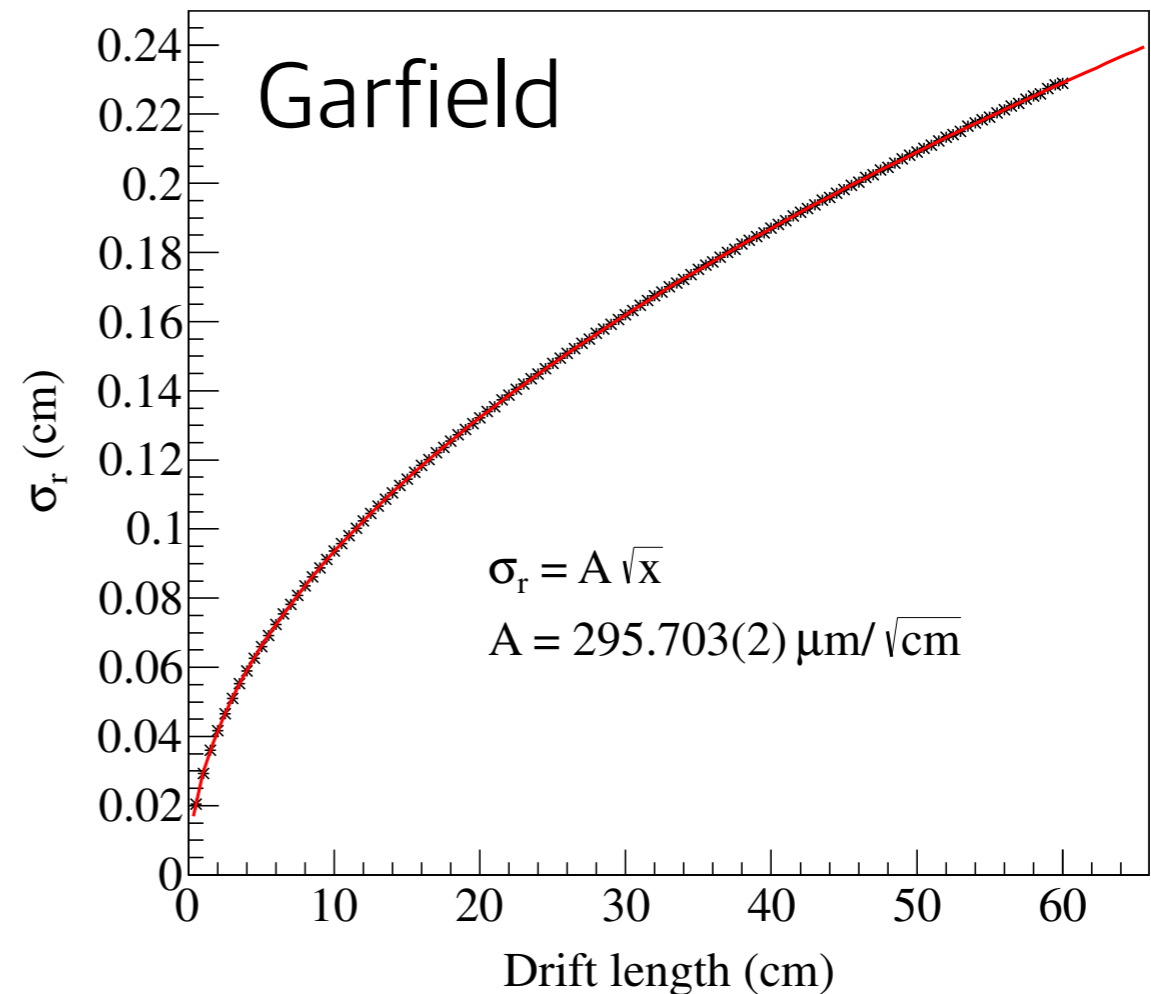
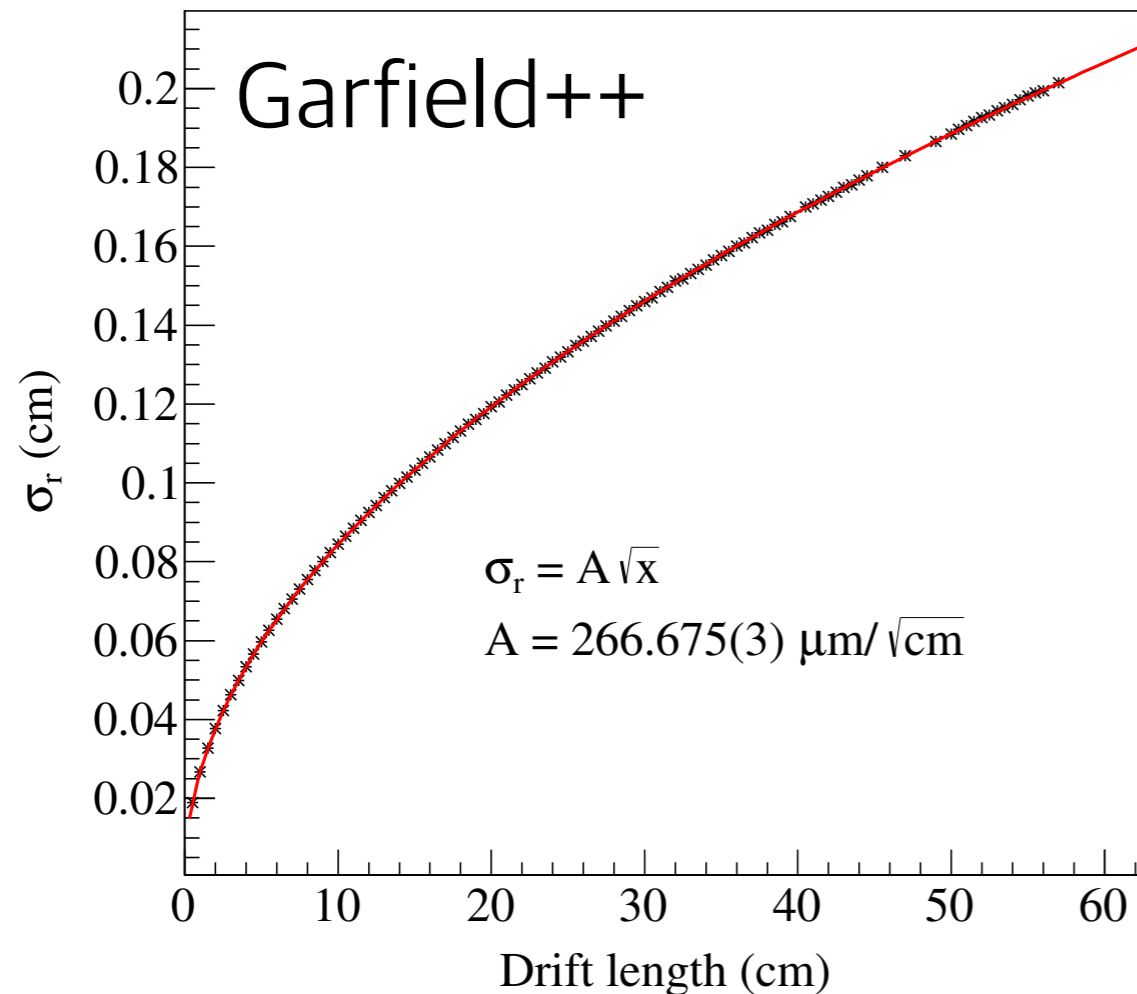


Detector schematic



Drift space simulation - Transverse diffusion

$$\text{Magboltz2: } \sigma_T = 206.91 \mu\text{m}/\sqrt{\text{cm}}$$



- All values are different.
- The difference appears when dealing with the magnetic field.



받는 사람: Genie Jhang

Re: Question on diffusion using garfieldpp

So, you're saying that when Garfield++ is running in microscopic tracking mode, it doesn't use the transport properties.

That's right - it takes the cross sections from Magboltz and then tracks the electrons using an algorithm that is largely inspired by Magboltz.

Garfield used (and still uses) the actual Magboltz tracking algorithm with minimal changes for the field - but Garfield++ uses a C++ version. Heinrich can tell you all about that.

Since I'm running Garfield++ using AvalancheMC class, it refers the values, right?

Avalanche MC should not be used at all for electrons - this is obsolete and replaced my microscopic tracking. The NC algorithm was badly inaccurate for B fields:

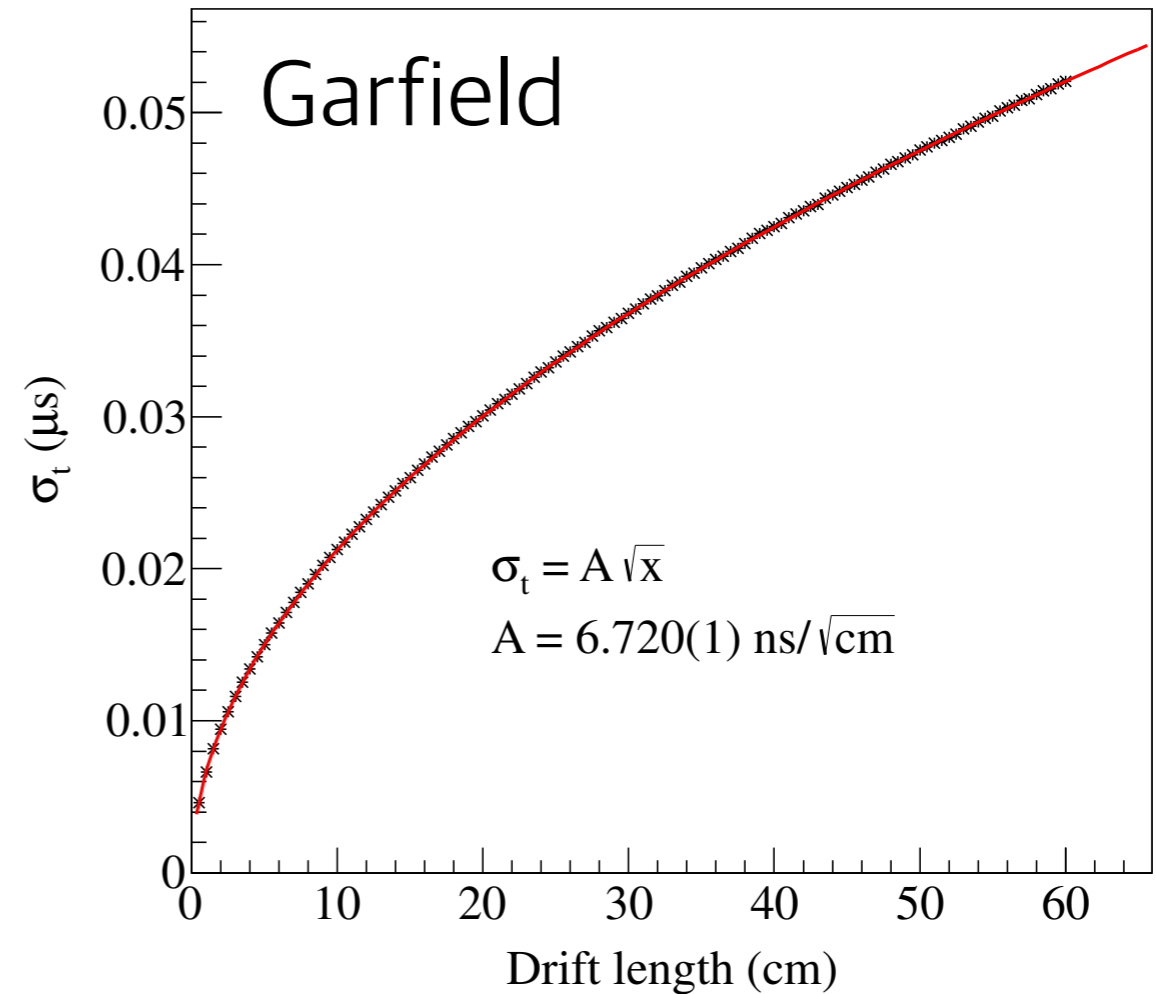
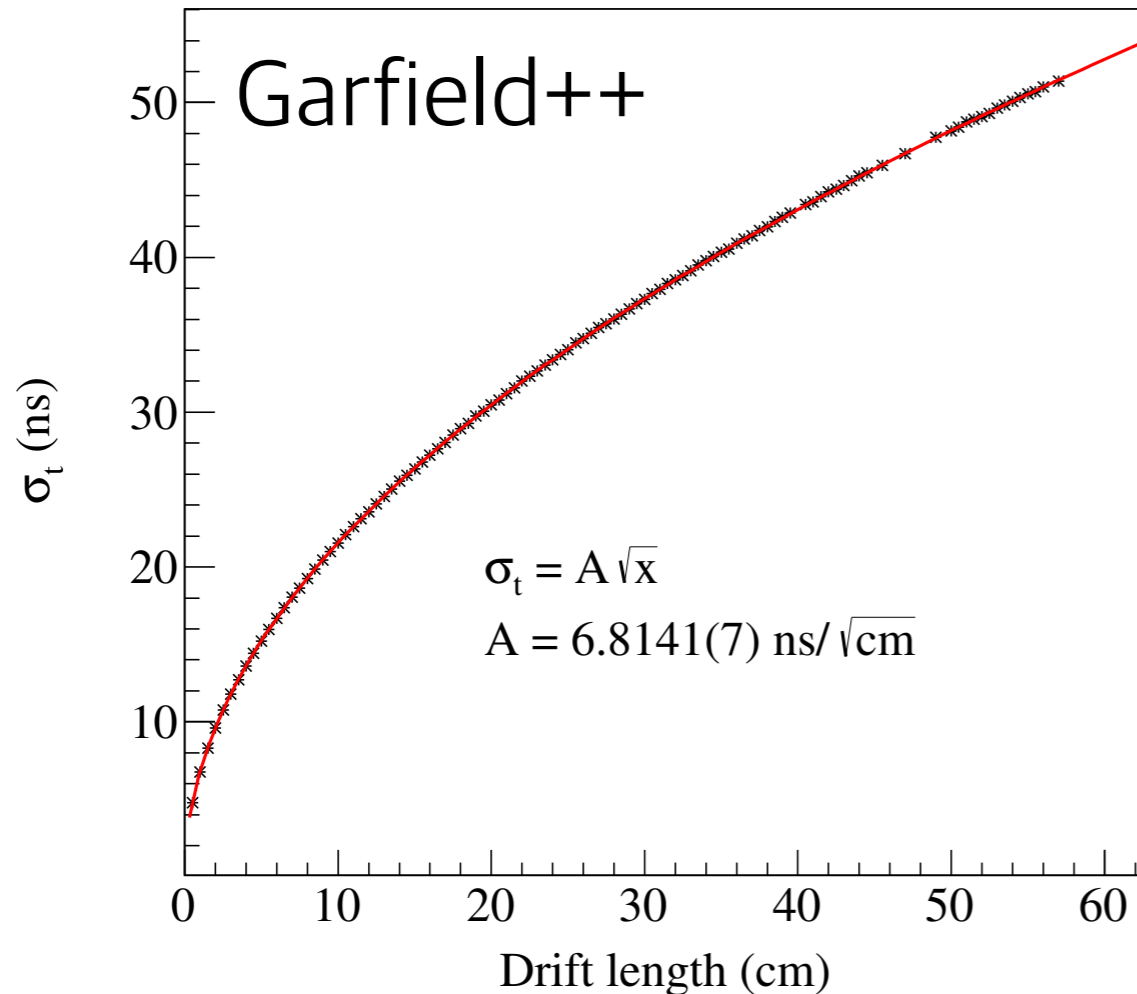
What does the last comment mean?

There are 3 (principal) algorithms: RKF for long distances, MC which was a failed attempt at doing microscopic tracking based on transport tables and the actual microscopic tracking method. In the Garfield 'notes' you'll find the explanation why MC fails for electrons.

For ions, one still uses MC but ions are fortunately not much affected by B fields. Currently most of our efforts are directed at ions and we hope to come up with better ion transport.

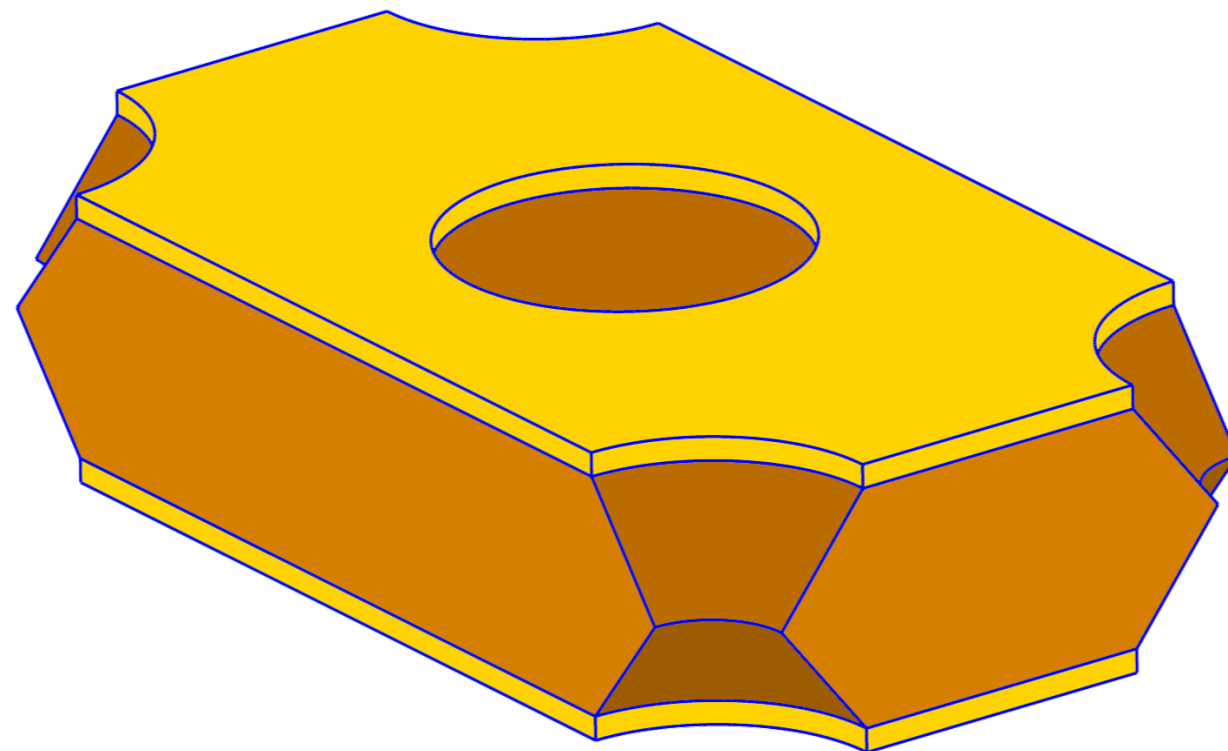
Drift space simulation - Longitudinal diffusion

$$\text{Magboltz2: } \sigma_L = 6.710 \text{ ns}/\sqrt{\text{cm}}$$



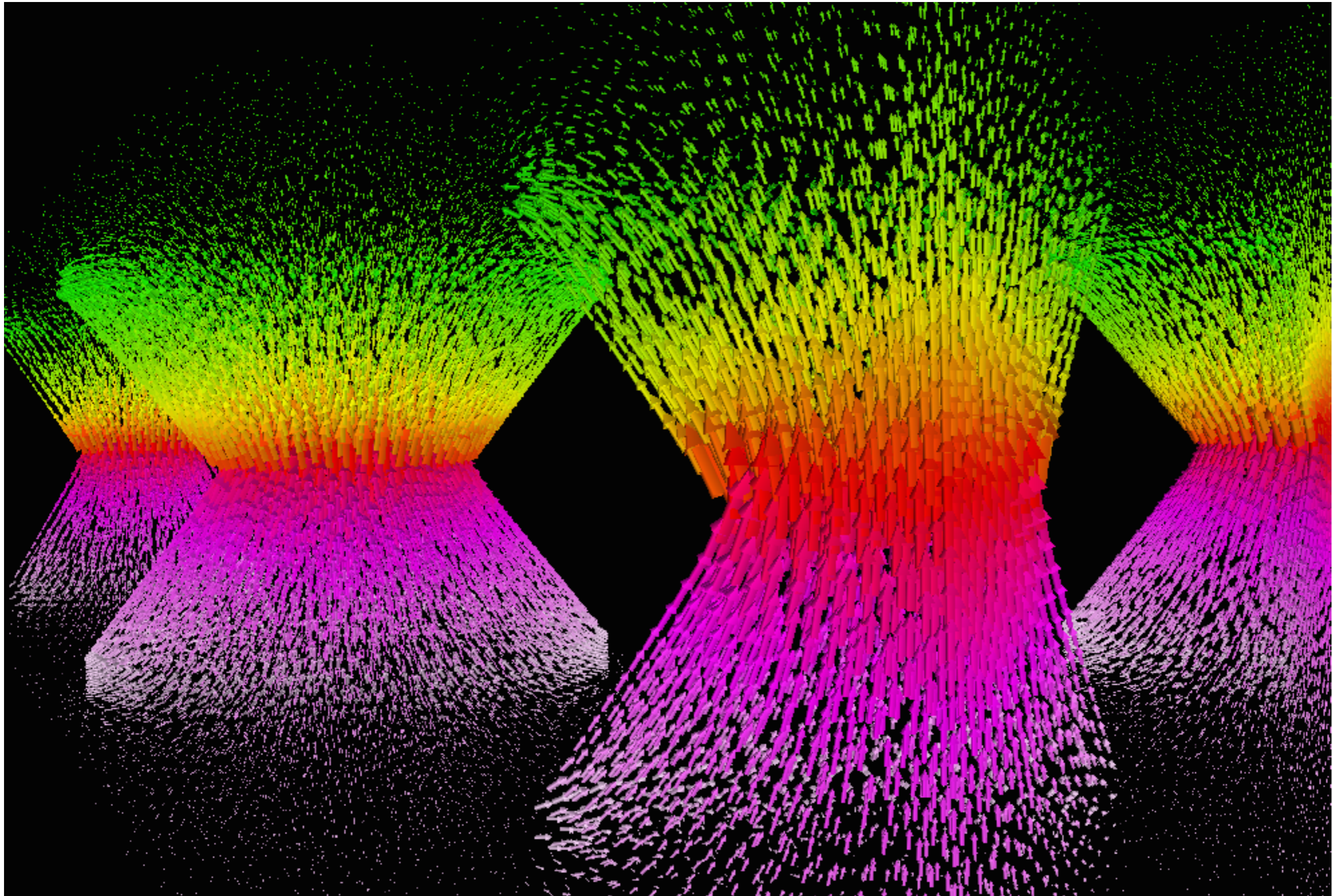
- Since the longitudinal direction are independent of the magnetic field, differences are not that large compared to the lateral dispersion case.

GEM dimensions

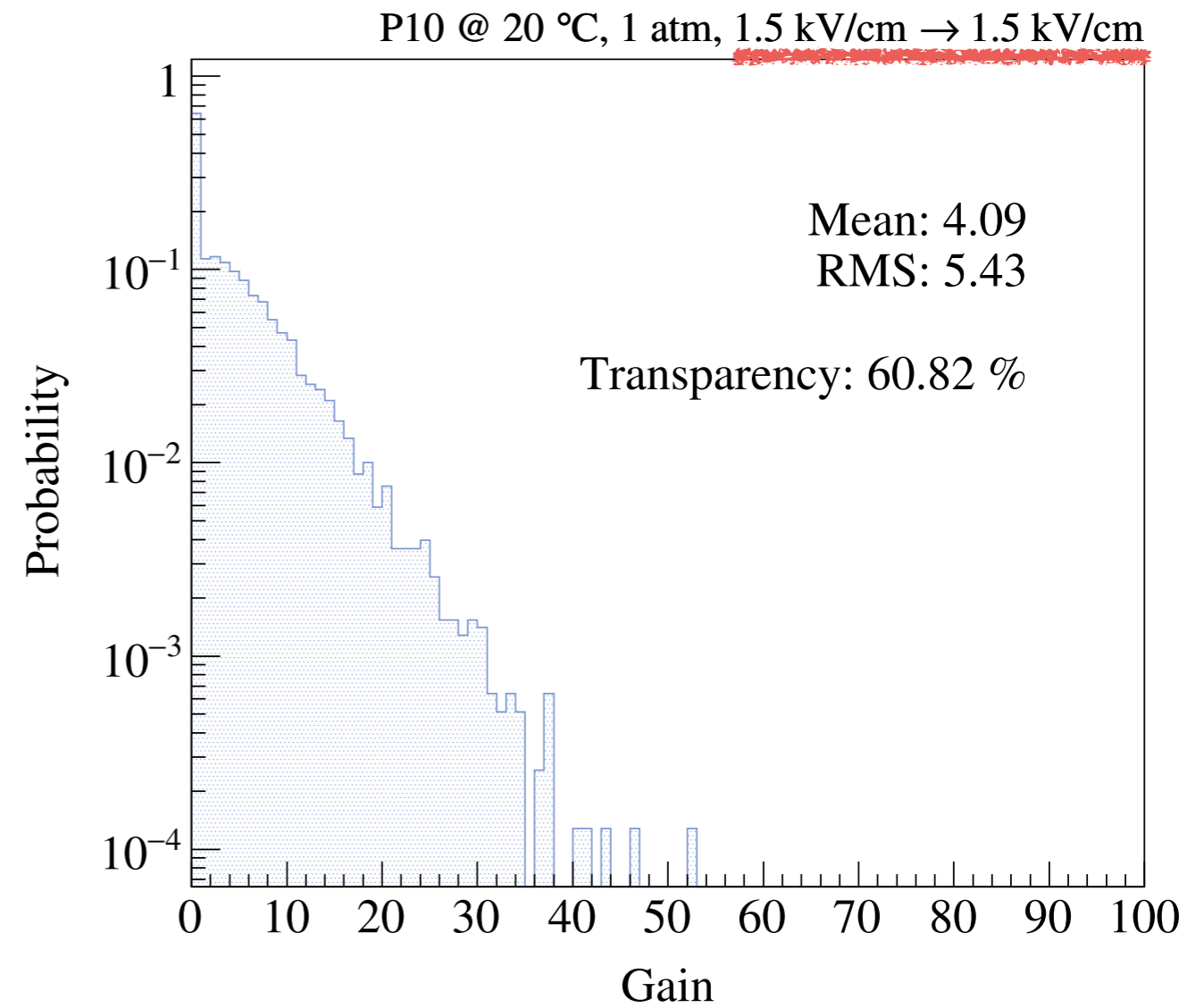
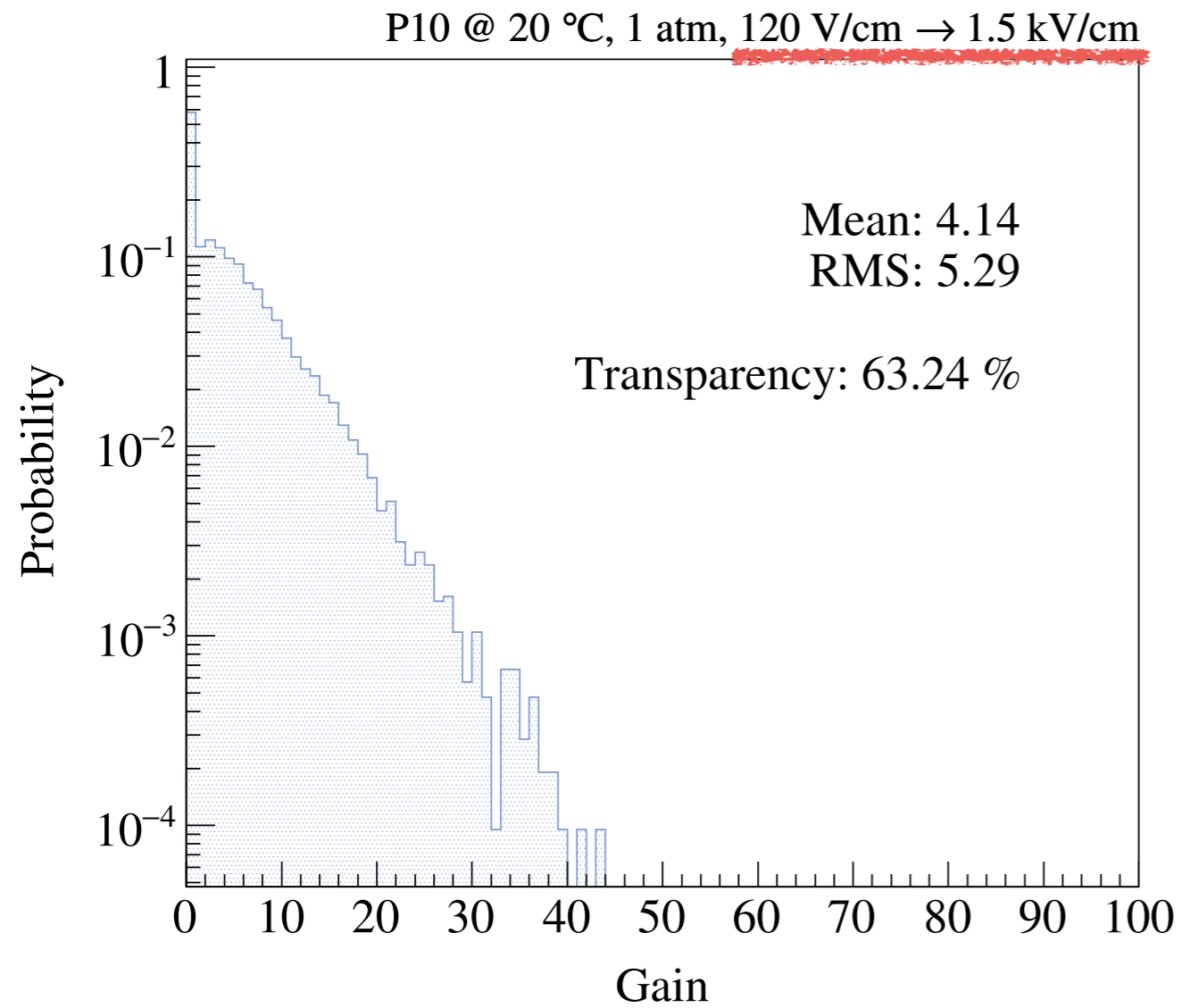


Hole pitch	140 μm
Outer diameter	75 μm
Inner diameter	35 μm
Kapton thickness	50 μm
Copper thickness	5 μm

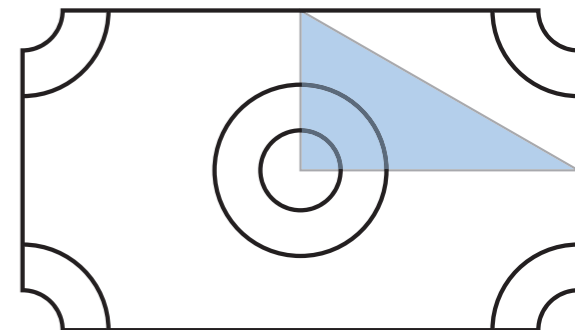
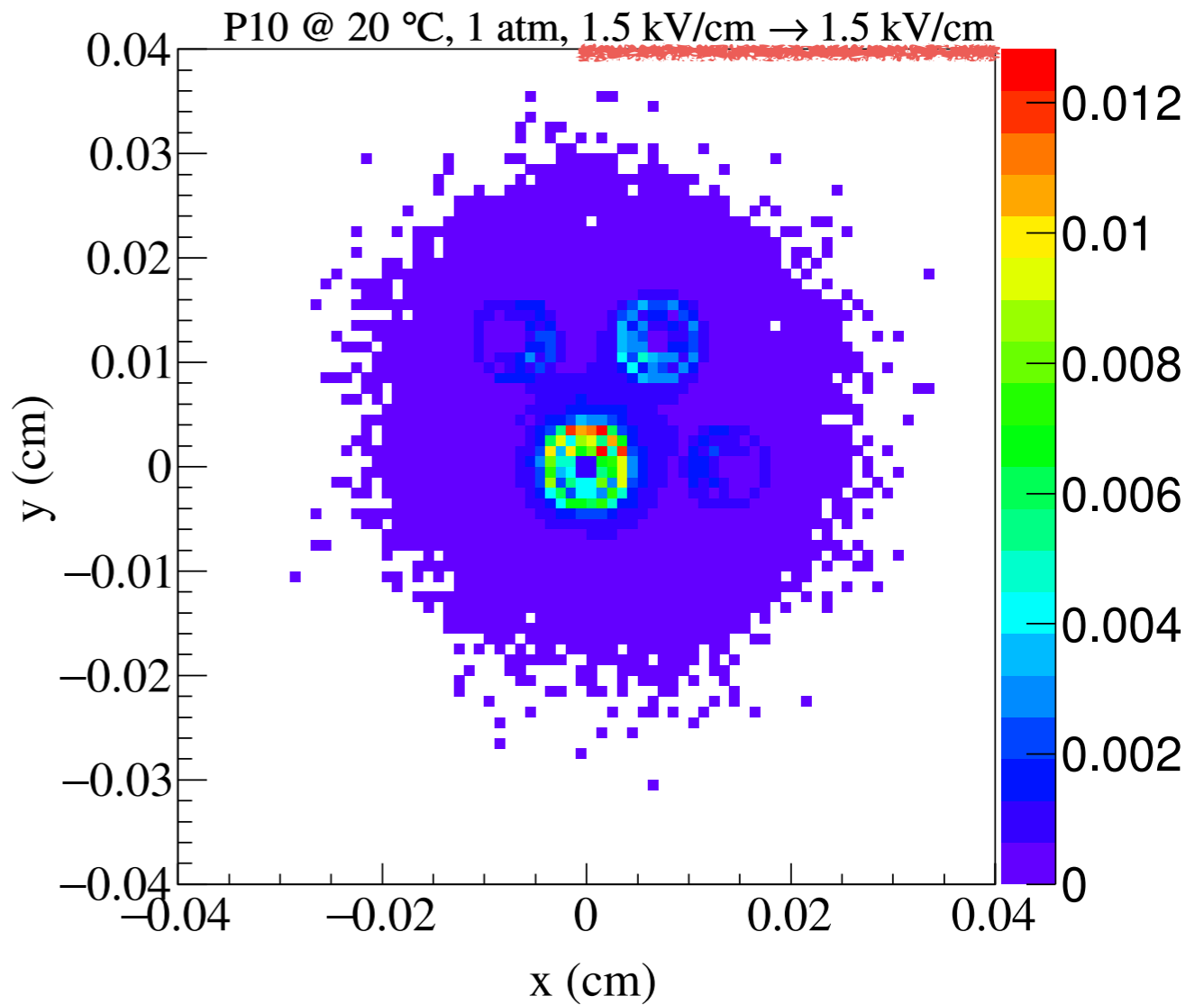
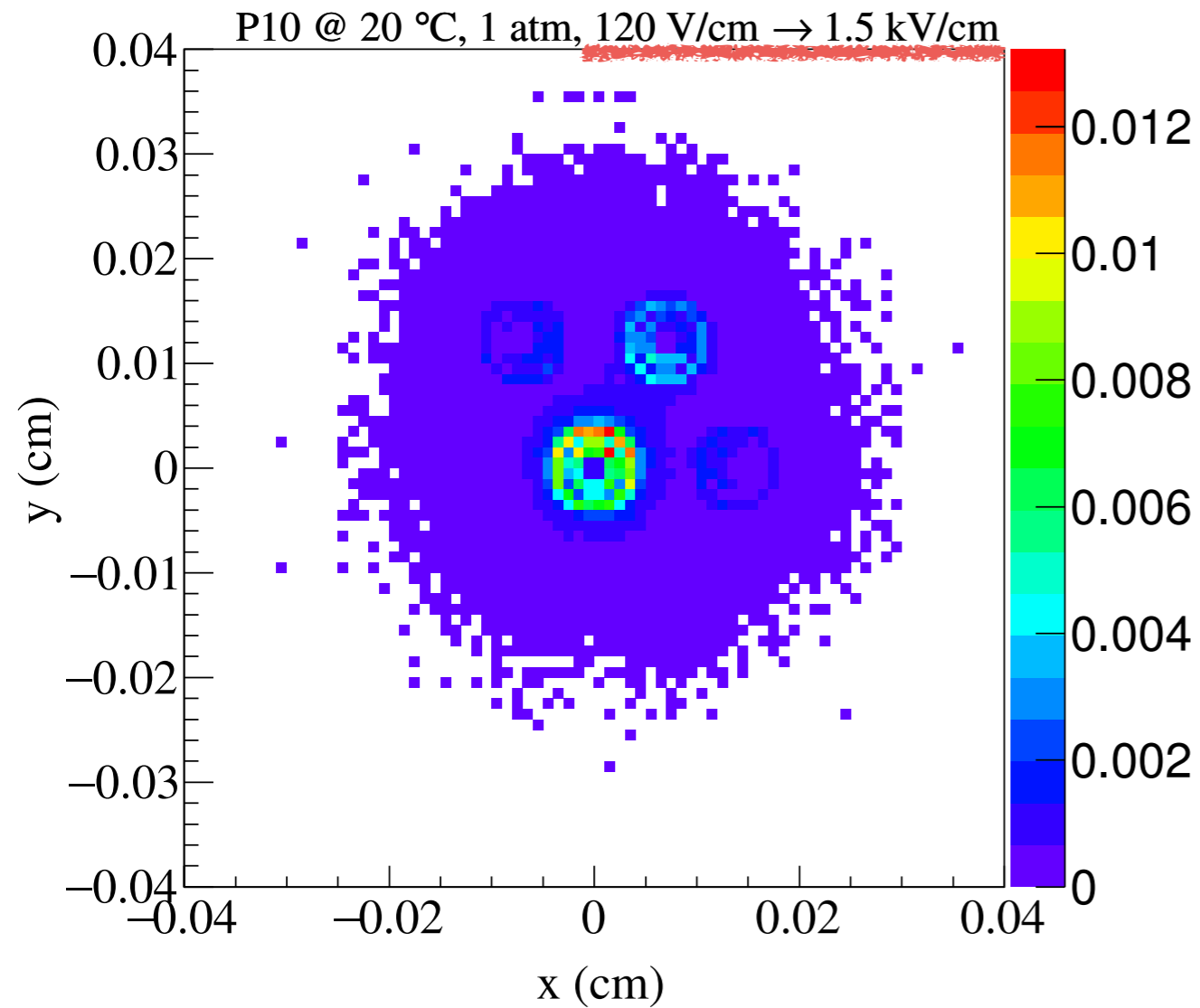
Electric field in GEM hole



GEM simulation - Gain

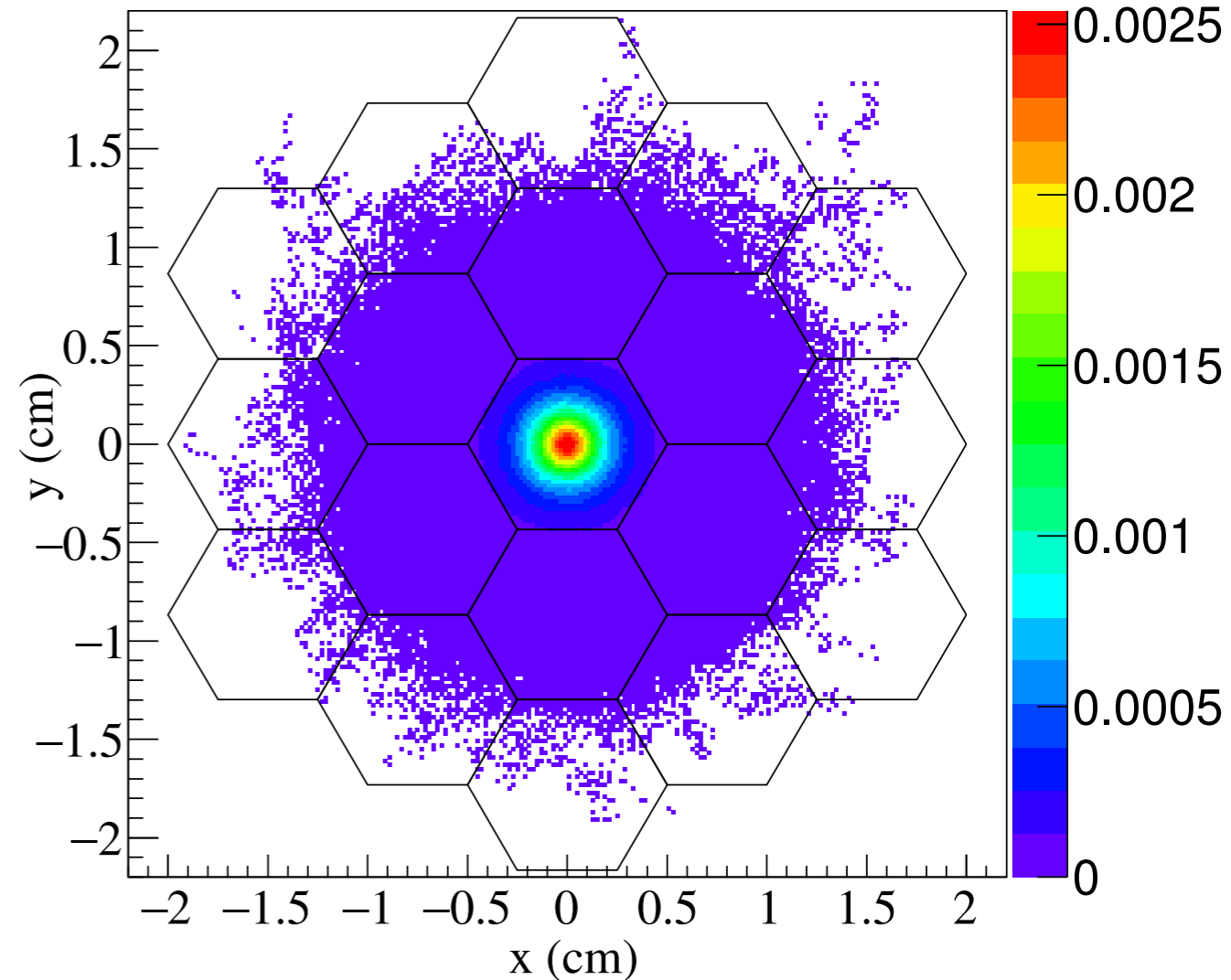
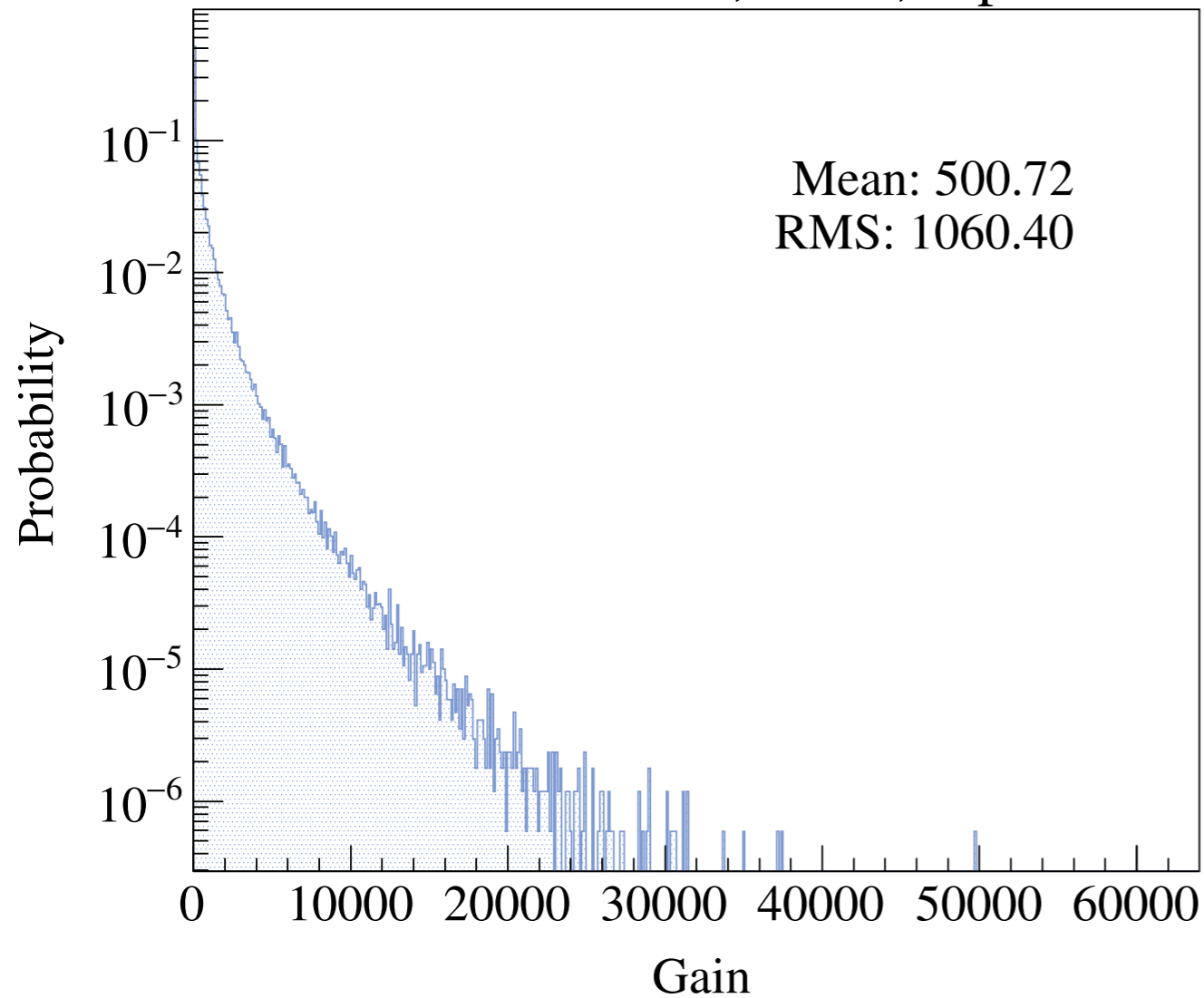


GEM simulation - diffusion



GEM simulation - Triple GEM

P10 @ 20 °C, 1 atm, triple-GEM



Parameter	120 V/cm	1500 V/cm
σ_T ($\mu\text{m}/\sqrt{\text{cm}}$)	206.91	539.91
σ_L ($\mu\text{m}/\sqrt{\text{cm}}$)	372.03	223.13
v_d (cm/ μs)	5.544	2.349